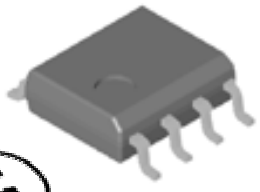
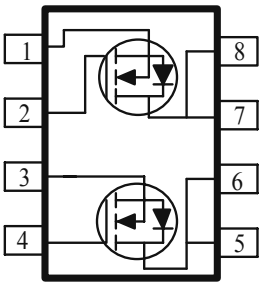
N-Channel 60-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ mΩ	I_D (A)
60	89 @ V_{GS} = 10V	±4.0
	104 @ V_{GS} = 4.5V	±3.7

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ESD Protected
2000V

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Units**
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[a]	T_A=25°C	I_D	±4.0	A
	T_A=70°C		±3.3	
Pulsed Drain Current[b]		I_{DM}	±25	
Continuous Source Current (Diode Conduction)[a]		I_S	2	A
Power Dissipation[a]	T_A=25°C	P_D	2.1	W
	T_A=70°C		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient[a]	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W
	t <= 5 sec		110	°C/W

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	uA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 55°C			10	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	20			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 4.0 A			89	mΩ
		V_{GS} = 4.5 V, I_D = 3.7 A			104	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 15 V, I_D = 4.0 A		11		S
Diode Forward Voltage	V_{SD}	I_S = 2.0 A, V_{GS} = 0 V		1.1		V
Pulsed Source Current (Body Diode)[A]	I_{SM}			5		A
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 30 V, V_{GS} = 4.5 V, I_D = 4.0 A		3.6		nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			1.3		
Switching						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 30 V, R_L = 30Ω , I_D = 1 A, V_{GEN} = 10 V		9		nS
Rise Time	t_r			10		
Turn-Off Delay Time	$t_{d(off)}$			21		
Fall-Time	t_f			8		

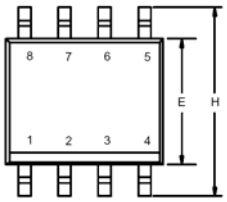
Notes

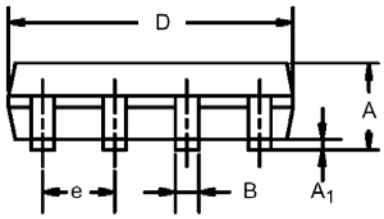
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

Package Information

SO-8: 8LEAD





Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°